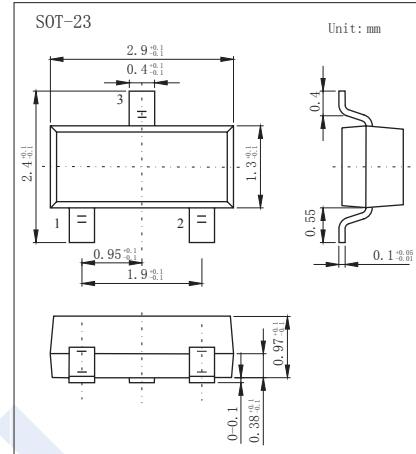
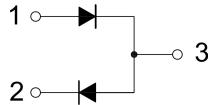


## Switching Diodes

### MMBD7000 (KMBD7000)

#### ■ Features

- Dual Swithching Diode
- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse Voltage	V <sub>RM</sub>	100	V
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	75	
Working Peak Reverse Voltage	V <sub>RWM</sub>		
RMS Reverse Voltage	V <sub>RMS</sub>	53	
Average Rectified Output Current	I <sub>O</sub>	200	mA
Non-Repetitive Peak Forward Surge Current @ t = 1us @ t = 1s	I <sub>FSM</sub>	2	A
		1	
Power Dissipation	P <sub>d</sub>	225	mW
Thermal Resistance Junction to Ambient	R <sub>θ JA</sub>	556	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 to 150	

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V <sub>R</sub>	I <sub>R</sub> = 100 uA	100			V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 mA			0.7	
		I <sub>F</sub> = 10 mA			0.82	
		I <sub>F</sub> = 100 mA			1.1	
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> = 50 V			1	uA
		V <sub>R</sub> = 100 V			3	
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> = 0 V, f= 1 MHz			2	pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>rr</sub> =0.1xI <sub>R</sub> , R <sub>L</sub> =100Ω			4	ns

#### ■ Marking

Marking	5C
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## Switching Diodes

### MMBD7000 (KMBD7000)

#### ■ Typical Characteristics

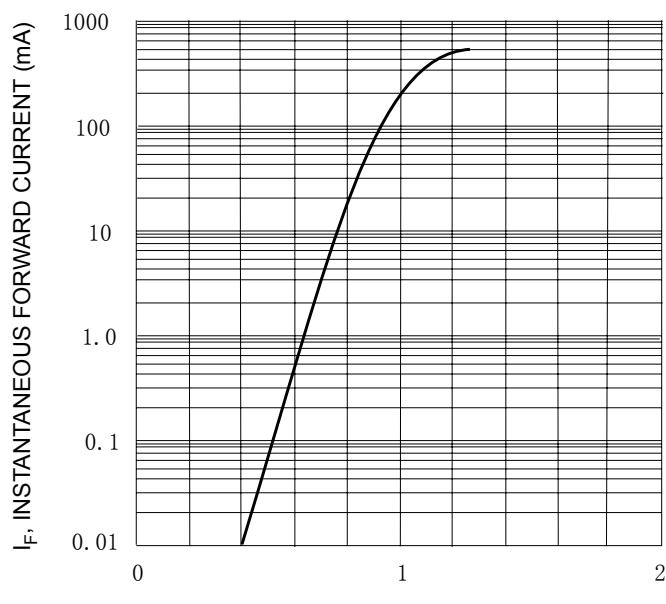


Fig. 1 Forward Characteristics

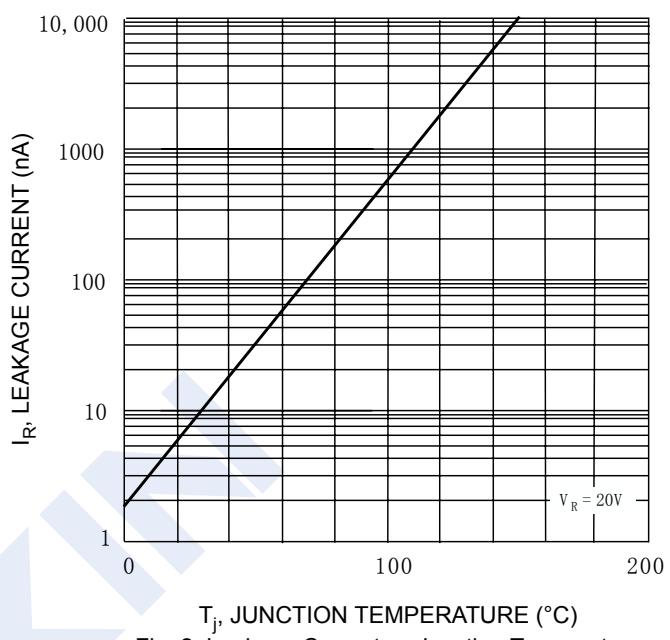


Fig. 2 Leakage Current vs Junction Temperature